

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT

APPLICANT(S): Osamu Goto, et al. . DOCKET NO.: 09792909-5625
SERIAL NO.: Unknown GROUP ART UNIT: Unknown
DATE FILED: June 25, 2003 EXAMINER: Unknown
INVENTION: "SEMICONDUCTOR LIGHT EMITTING DEVICE, ITS
MANUFACTURING METHOD, SEMICONDUCTOR DEVICE,
AND ITS MANUFACTURING METHOD"

Mail Stop: PCT
Commissioner for Patents
P.O. Box 1450
Arlington, VA 22313-1450

S I R:

In accordance with the provisions of 37 C.F.R. § 1.56, Applicants request that citation and examination of the references identified on the attached PTO-1449 form, copies of which are enclosed herewith in accordance with 37 C.F.R. §1.98, be made during the course of examination of the above-referenced application for United States Letters Patent.

I. SUBMITTED US PATENT REFERENCES

<u>Number</u>	<u>Country</u>	<u>Date of Publication</u>
6,060,335	U.S.	May 9, 2000

II. SUBMITTED FOREIGN PATENT REFERENCES

<u>Number</u>	<u>Country</u>	<u>Date of Publication</u>
JP11-54794	Japan	February 26, 1999
JP09-266326	Japan	October 7, 1997
JP11-243251	Japan	September 7, 1999
EP 0 803 916	Europe	October 3, 1999

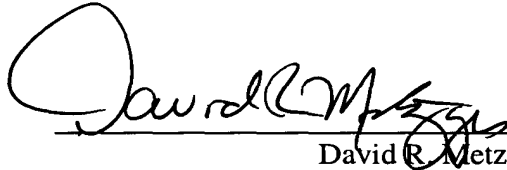
III. OTHER ITEMS OF INFORMATION

AT Shuji Nakamura, et al., "*Characteristics of InGaN multi-quantum-well-structure laser diodes*", Applied Physics Letters, 1996, Vol. 68, No. 23, pp. 3269-3271.

IV. EXPLANATION OF RELEVANCE

The above-identified references were cited in the Japanese Patent Office Search Report of March 26, 2002, in counterpart PCT/JP01/11536. A copy of the Search Report is submitted herewith.

Submitted by,



(Reg. 32,919)

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37 CFR 1.501
 INFORMATION DISCLOSURE STATEMENT
 IN A PATENT
 (use several sheets if necessary)

Docket No.
 09792909-5625

Serial No.

Applicants:
 Osamu Goto, et al.

Filing Date
 June 25, 2003

Group Art Unit

U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If appropriate
	AA	6,060,335	5-9-00	Rennie			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AH	JP11-54794	2-26-99	Japan			Abstract	
	AI	JP09-266326	10-7-97	Japan			Abstract	
	AJ	JP11-243251	9-7-99	Japan			Abstract	
	AK	EP 0 803 916	10-29-99	Europe				
	AL							
	AM							
	AN							
	AO							
	AP							
	AQ							
	AR							
	AS							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	AT	Shuji Nakamura, et al., "Characteristics of InGaN multi-quantum-well-structure laser diodes", Applied Physics Letters, 1996, Vol. 68, No. 23, pp. 3269-3271
	AU	
	AV	
	AW	
	AX	
	AY	
	AZ	

Examiner

Date Considered

***EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.